Ordering number : ENA0578A



SANYO Semiconductors DATA SHEET

2SC6118LS

NPN Triple Diffused Planar Silicon Transistor

Color TV Horizontal Deflection Output Applications

Features

- · High speed.
- High breakdown voltage (V_{CBO}=1500V).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- · On-chip damper diode.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO	COM	1500	V
Collector-to-Emitter Voltage	VCEO	.0.0	800	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		8	Α
Collector Current (Pulse)	ICP		20	Α
Collector Dissipation	De		2.0	W
	PC	Tc=25°C	35	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ІСВО	V _{CB} =800V, I _E =0A			10	μΑ
Collector Cutoff Current	ICES	VCE=1500V, RBE=0Ω			1.0	mA
Collector Sustain Voltage	VCEO(sus)	I _C =100mA, I _B =0A	800			V
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A	40		130	mA

Continued on next page.

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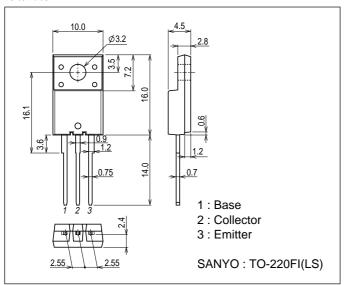
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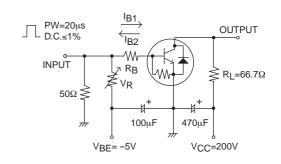
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =4.5A, I _B =0.9A			2	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =4.5A, I _B =0.9A			1.5	V
DC Current Gain	hFE1	V _{CE} =5V, I _C =1A	10			
	hFE2	V _{CE} =5V, I _C =5A	5.3		7.5	
Diode Forward Voltage	٧F	I _{EC} =7A			2	V
Fall Time	tf	I _C =3A, I _{B1} =0.6A, I _{B2} =-1.2A			0.2	μS

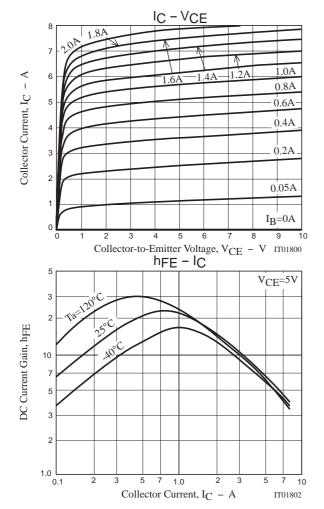
Package Dimensions

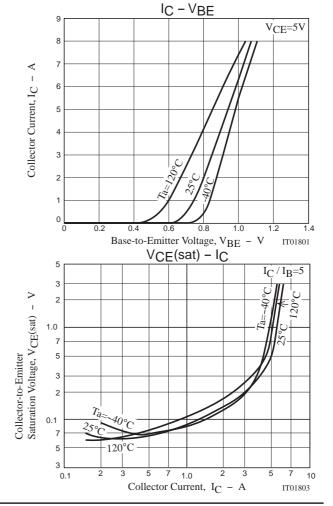
unit : mm (typ) 7509-003



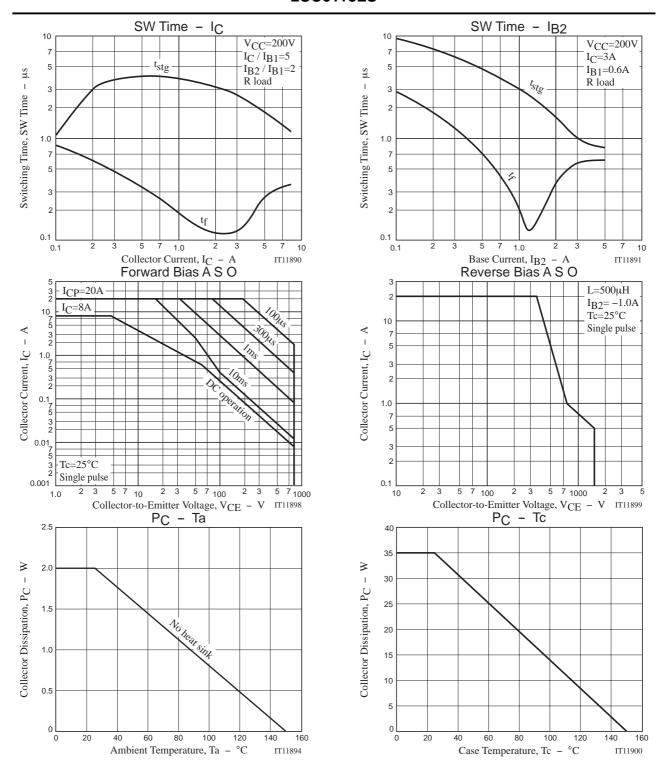
Switching Time Test Circuit







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